

### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE0102 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

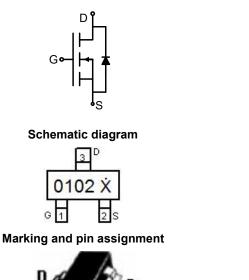
•  $V_{DS} = 100V, I_D = 2A$ 

$$\begin{split} R_{DS(ON)} <& 230 m\Omega \ @\ V_{GS} =& 10V \quad (Typ:190 m\Omega) \\ R_{DS(ON)} <& 250 m\Omega \ @\ V_{GS} =& 4.5V \quad (Typ:200 m\Omega) \end{split}$$

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

## **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply





SOT-23 top view

# **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0102 X	NCE0102	SOT-23	Ø180mm	8 mm	3000 units

# Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	I <sub>D</sub>	2	Α	
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	1.4	Α	
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	8	Α	
Maximum Power Dissipation	P <sub>D</sub>	1.25	W	
Avalanche Current (Note 1)	I <sub>AR</sub>	2	Α	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	2.45	mJ	
Reverse diode dv/dt, V <sub>DS</sub> ≤80 V, I <sub>SD</sub> <i<sub>D</i<sub>	dv/dt	15	V/ns	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C	

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Ambient (Note 2)	R <sub>θJA</sub>	100	°C/W
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# Electrical Characteristics (T<sub>A</sub>=25 $^{\circ}$ C unless otherwise noted)

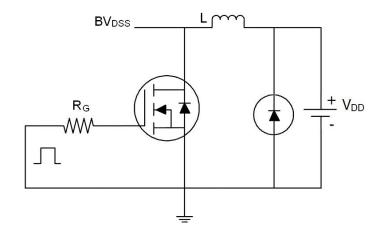
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			'	'		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100	110	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.2	1.8	2.5	V
Davis Course On Otata Basistana		V <sub>GS</sub> =10V, I <sub>D</sub> =2A	-	190	230	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	200	250	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =2A	1	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ 50\/\/ 0\/	-	360.6	-	PF
Output Capacitance	Coss	$V_{DS}=50V, V_{GS}=0V,$	-	24.6	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	13	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50V, $R_L$ =25 $\Omega$	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =1 $\Omega$	-	12	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ F0\/ L 0.4	-	12.0		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=50V,I_{D}=2A,$	-	1.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	2.9	-	nC
Drain-Source Diode Characteristics				•		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	2	Α

#### Notes:

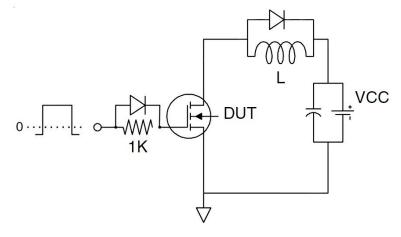
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.**EAS condition : Tj=25 $^{\circ}$ C,V<sub>DD</sub>=50V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

# **Test Circuit**

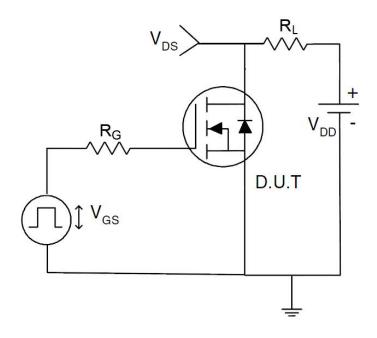
# 1) Eas test circuit



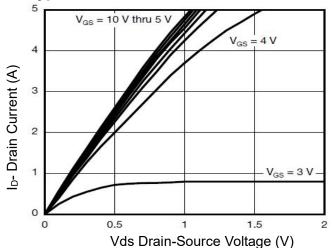
## 2) Gate charge test circuit



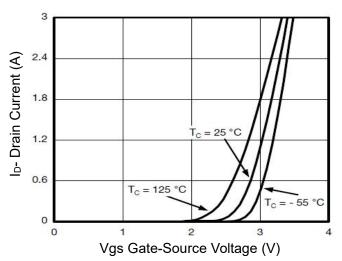
### 3) Switch Time Test Circuit



# **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

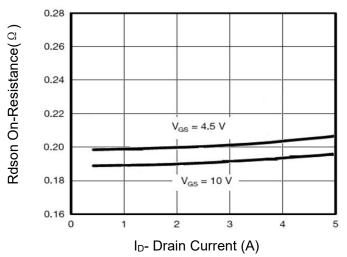


Figure 3 Rdson-Drain Current

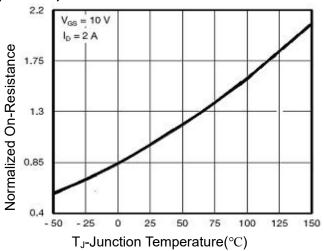


Figure 4 Rdson-JunctionTemperature

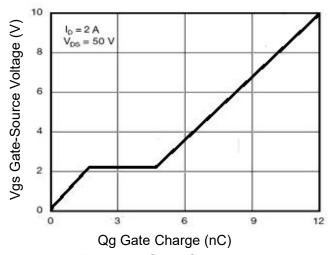


Figure 5 Gate Charge

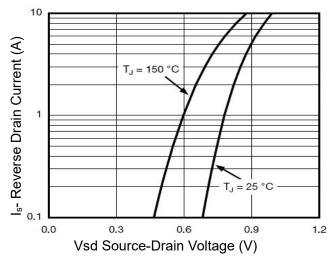


Figure 6 Source- Drain Diode Forward



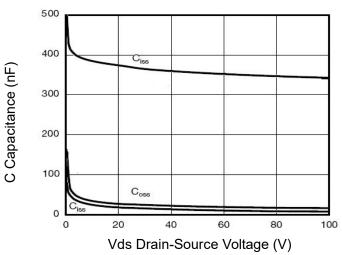


Figure 7 Capacitance vs Vds

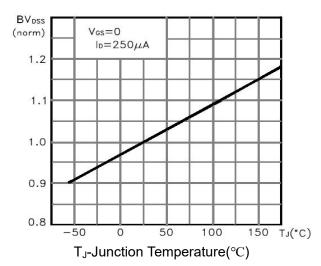
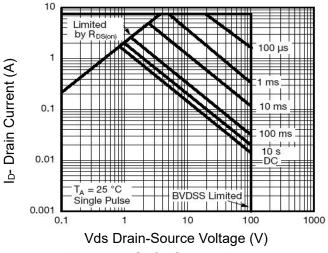


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 

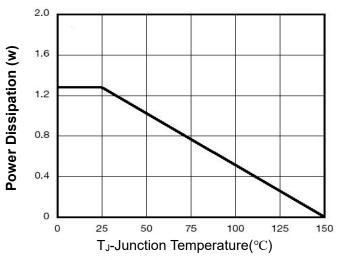
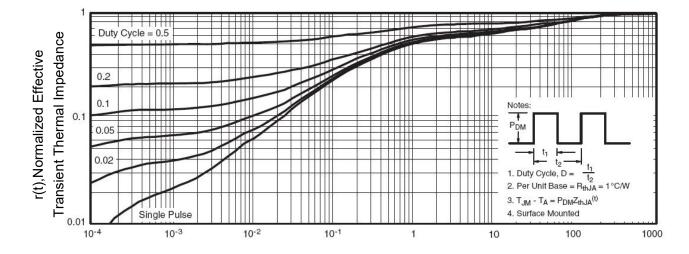


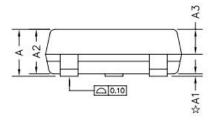
Figure 10 Power De-rati

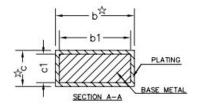


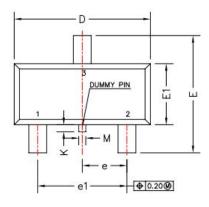
Square Wave Pluse Duration(sec)

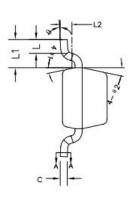
**Figure 11 Normalized Maximum Transient Thermal Impedance** 

# **SOT-23 Package Information**









Cumbal	Millimeters			
Symbol	Min.	Max.		
Α	0.89	1.12		
A1	0.01	0.10		
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6	REF		
L2	0.25BSC			
М	0.10	0.25		
K	0.00	0.25		
θ	0°	8°		
θ1	10°	14°		
θ2	10°	14°		

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